



HERF1001G - HERF1008G

10.0AMPS. Isolated Glass Passivated High Efficient Rectifiers

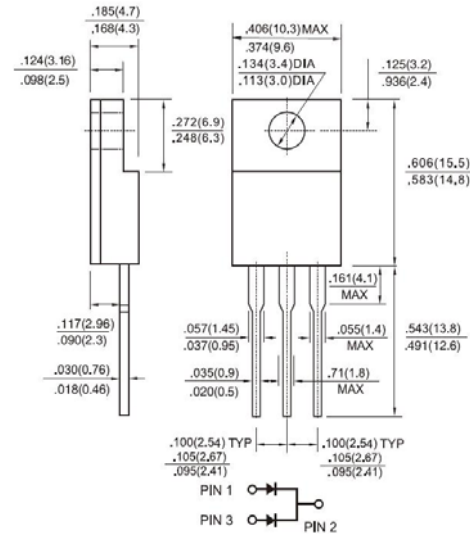
ITO-220AB

Features

- ✧ UL Recognized File # E-326243
- ✧ Glass passivated chip junction
- ✧ High efficiency, Low VF
- ✧ High current capability
- ✧ High reliability
- ✧ High surge current capability
- ✧ For use in low voltage, high frequency inverter, free wheeling, and polarity protection application
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode

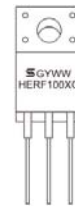
Mechanical Data

- ✧ Case: ITO-220AB Molded plastic
- ✧ Epoxy: UL 94V-0 rate flame retardant
- ✧ Terminals: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- ✧ Polarity: As marked
- ✧ High temperature soldering guaranteed: 260 °C /10s /0.25", (6.35mm) from case
- ✧ Mounting torque: 5 in-lbs. max
- ✧ Weight: 2.24 grams



Dimensions in inches and (millimeters)

Marking Diagram



- HERF100XG = Specific Device Code
G = Green Compound
Y = Year
WW = Work Week

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	HERF 1001G	HERF 1002G	HERF 1003G	HERF 1004G	HERF 1005G	HERF 1006G	HERF 1007G	HERF 1008G	Unit
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current @ T _C =100°C	I _{F(AV)}	10.0								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	125								A
Maximum Instantaneous Forward Voltage (Note 1) @ 5.0A	V _F	1.0				1.3	1.7			V
Maximum Reverse Current @ Rated VR T _A =25 °C T _A =125 °C	I _R	10 400								uA
Maximum Reverse Recovery Time (Note 2)	T _{rr}	50					80			nS
Typical Junction Capacitance (Note 3)	C _j	60					40			pF
Typical Thermal Resistance	R _{θJC}	3								°C/W
Operating Temperature Range	T _J	- 65 to + 150								°C
Storage Temperature Range	T _{STG}	- 65 to + 150								°C

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2: Reverse Recovery Test Conditions: $I_F=0.5A$, $I_R=1.0A$, $IRR=0.25A$

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

RATINGS AND CHARACTERISTIC CURVES (HERF1001G THRU HERF1008G)

FIG.1 FORWARD CURRENT DERATING CURVE

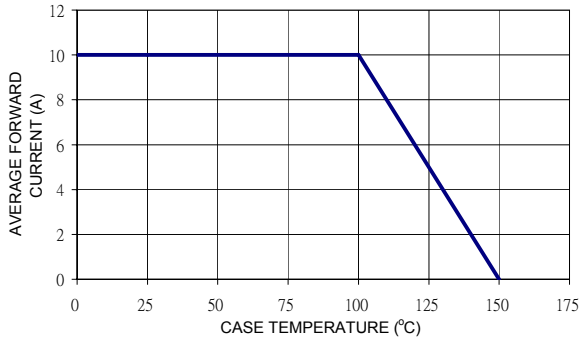


FIG. 2 TYPICAL REVERSE CHARACTERISTICS

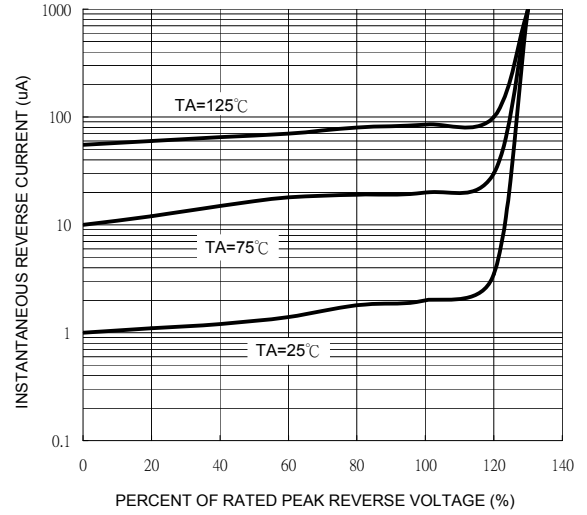


FIG. 3 MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

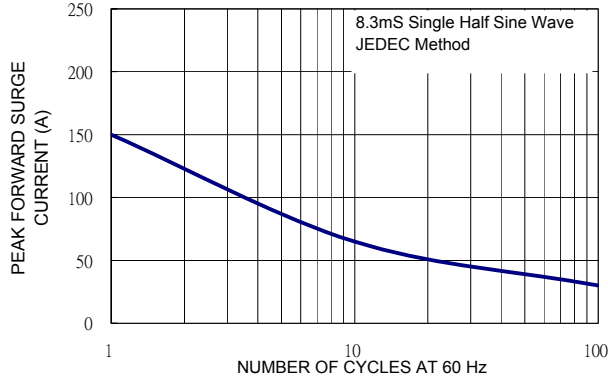


FIG. 5 TYPICAL FORWARD CHARACTERISTICS

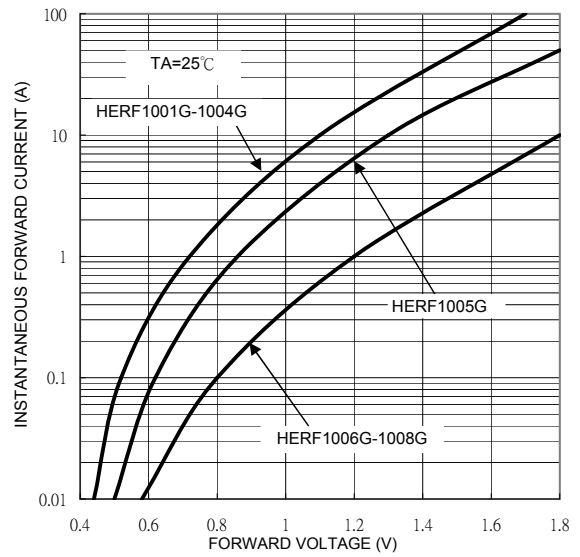


FIG. 4 TYPICAL JUNCTION CAPACITANCE

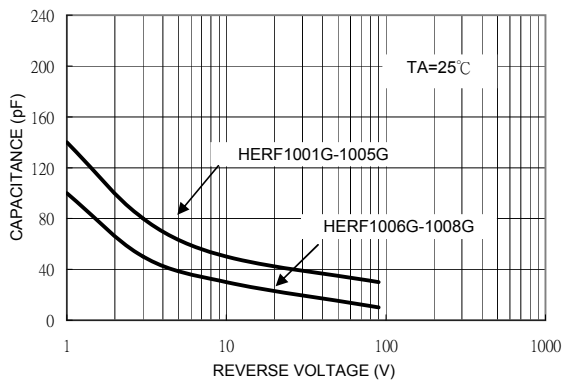


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

